U.S. Department of Commerce, Patent and Trademark Office	Atty. Docket No.	Serial No.
	M-15327 US	10/772,932
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Chia-Shun Hsiao et al.	
	Filing Date	Group
	Feb. 4, 2004	2818

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CAL	B	6,403,417	06-2002	Chien et al.			—
CAL	C	6,451,708	09-2002	Ha			—
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

CAL	L	Naruke, K.; Yamada, S.; Obi, E.; Taguchi, S.; and Wada, M. "A New Flash-Erase EEPROM Cell with A Sidewall Select-Gate On Its Source Side," 1989 IEEE, pp. 604-606.
CAL	M	Wu, A.T.; Chan T.Y.; Ko, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source-Side Injection," 1986 IEEE, 584-587.
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	7/25/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Departme of ce, Patent and Trademark Office	Atty. Docket No.	Serial No.
	M-15327 US	Unassigned
INFORM TIO SCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
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	Filing Date	Group
	Herewith	Unassigned

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CAL	AA	03/0067806	10 Apr. 2003	Tuan	—	—	—
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Foreign Patent Documents

		Document	Date	Country	Class	Subclass	Translation Yes	Translation No
	AC							
	AT							

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CAL	Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on Its Source Side", M Technical Digest 1989, pages 603-606.
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